

Low-frequency and dual-band microwave absorption properties of novel VB-group disulphides (3R–TaS₂) nanosheets

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ABSTRACT

As electromagnetic technology advances and demand for electronic devices grows, concerns about electromagnetic pollution intensify. This has spurred focused research on innovative electromagnetic absorbers, particularly chalcogenides, noted for their superior absorption capabilities. In this study, we successfully synthesize 3R–TaS₂ nanosheets using a straightforward calcination method for the first time. These nanosheets exhibit significant absorption capabilities in both the C-band (4–8 GHz) and Ku-band (12–18 GHz) frequency ranges. By optimizing the calcination process, the complex permittivity of TaS₂ is enhanced, specifically for those synthesized at 1000 °C for 24 h. The nanosheets possess dual-band absorption properties, with a notable minimum reflection loss (RL_{min}) of –41.4 dB in the C-band, and an average absorption intensity exceeding 10 dB in C- and Ku-bands, in the absorbers with a thickness of 5.6 mm. Additionally, the 3R–TaS₂ nanosheets are demonstrated to have an effective absorption bandwidth of 5.04 GHz (3.84–8.88 GHz) in the absorbers with thicknesses of 3.5–5.5 mm. The results highlight the multiple reflection effects in 3R–TaS₂ as caused by their stacked structures, which could be promising low-frequency absorbers.

1. Introduction

In modern communication and defense systems, electromagnetic wave (EMW) absorbing materials have attracted attention due to their crucial role in reducing electromagnetic interference and enhancing the stealth and safety of electronic devices [1–4]. With the rapid advancement of wireless communication technologies, the demand for efficient EMW absorbing materials is rapidly growing, especially in the areas of low-frequency [5] and dual-band applications [6]. The research on EMW absorbing materials focuses not only on improving absorption rates but also on achieving light weight, thin thickness, and broad bandwidth coverage. Despite the exploration of a variety of materials for microwave absorption, it is a grand challenge that all these characteristics are achieved comprehensively.

Transition metal disulfides (TMDs), owing to their unique electronic structures and physical properties, have demonstrated significant

potential for applications in EMW absorption [7–10]. In particular, TMDs with transition metals of VB group, such as vanadium disulfide (VS₂) [6, 11–14] and niobium disulfide (NbS₂) [15–18], have shown their effectiveness in controlling EMW propagation and absorption. Coaxially stacked VS₂ nanosheets (CSVNs), prepared via a simple one-step hydrothermal method, have shown good absorption performance in both the C-band (4–8 GHz) and Ku-band (12–18 GHz) [6]. The VS₂/NiO composite, formed by uniformly attaching nickel oxide (NiO) onto VS₂ nanosheets, exhibited significant EMW absorption effects [11]. Moreover, through coating biomass-derived glucose carbon (GDC) onto stacked VS₂ nanosheets and treating the VS₂/GDC composite by high-temperature carbonization, the effective absorption bandwidth and environmental stability of the composite material were significantly enhanced [12]. NbS₂ is a novel TMD that has been developed for EMW absorption. For instance, NbS₂ nanosheet-based EMW absorbers, prepared via a simple one-step solvothermal method, achieved a tunable

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frequency band [16]. Meanwhile, the electromagnetic properties of NbS₂ were successfully modulated by intercalating transition metals (Fe, Co, Ni) [17], tuning their EMW absorption properties. Hu et al. [19] synthesized d-Mo₂TiC₂T_x MXene through a combination of HF acid etching and intercalation layer delayering, enhancing the synergistic effect of dielectric-magnetic loss and matching impedance in a 2D/2D structure with multiple scattering by supporting Ni through various solvothermal reduction pathways. In addition to metallic materials, non-metallic material adhesives can also serve as ideal materials for high-strength electromagnetic wave absorption. They prepared multifunctional SiC nanofiber aerogel springs (SiC NFAS) via a simple thermochemical process, demonstrating good superelasticity and cyclic fatigue resistance [20]. By utilizing freeze casting technology, followed by carbonization and calcination processes, they successfully synthesized a multifunctional monolithic SiC ceramic aerogel with excellent mechanical properties, ideal impedance matching, and efficient EMW absorption performance [21]. This work paves the way for the development and widespread application of high-strength electromagnetic absorbing materials.

Compared to other VB-group TMDs, tantalum disulfide (TaS₂) exhibits unique advantages in EMW absorption due to its distinctive electronic structure, phase transition characteristics, dielectric loss capabilities, chemical and thermal stability, as well as its adjustable interlayer spacing and layered structure [22–32]. However, current research on TaS₂ in the EMW absorption field primarily focuses on those with 1T or 2H phase, mostly utilizing commercial TaS₂ for the modification of compositions of microwave absorbing materials, with very few studies on the fabrication process of TaS₂. Wan et al. [33] reported the preparation and EMW absorption of ultra-thin 1T-TaS₂/Co(Cp)₂ microwave absorbing materials through mixing TaS₂/Co(Cp)₂ superlattice. The dynamic Ta–Co dipoles, dielectric matching and ferromagnetism under high dielectric constants were achieved in 1T-TaS₂/Co(Cp)₂, thereby enhancing their microwave absorption performance. Sun et al. [34] studied re-stacked 2H-TaS₂ nanosheets resulting from the van der Waals interactions in an intercalated manner, which were then combined with polymer fibers to improve their electrical conductivity and electromagnetic interference shielding effectiveness. These studies mainly focus on the wave absorption and shielding properties of TaS₂ composites, while there has been no report on the fabrication process and EMW absorption performance of the unmodified TaS₂ with a 3R phase. Therefore, in this work, we develop TaS₂ nanosheets with a substantial amount of 3R phase as a microwave absorbing material for the first time. By adjusting the reaction temperature and shortening the reaction time, the nanosheets are found to exhibit exceptional EMW absorption performance, particularly in the C band, showing a minimum reflection loss of −41.4 dB. Notably, these unblended TaS₂ nanosheets exhibit dual-band absorption characteristics in both the C- and Ku-bands. The abundant active sites and stacked nanosheets of TaS₂ provide multiple reflection interfaces for EMW absorption, offering new possibilities for the development of TaS₂-based EMW absorbers. This work could facilitate a comprehensive understanding on the EMW loss mechanisms in VB-group TMDs absorbers.

2. Experimental details

2.1. Preparation of TaS₂ nanosheet

Firstly, the mass (1.7911 g) of tantalum pentachloride (TaCl₅, Shanghai Aladdin Reagent Co., Ltd., China) was measured, serving as a reference for the determination of the requisite dosage of thioacetamide (CH₃CSNH₂, Tianjin Guangfu Fine Chemical Co., Ltd., China). The mass ratio of TaCl₅ to CH₃CSNH₂ was 1:2, while additional CH₃CSNH₂ was added to ensure the reaction could be complete. The two substances were transferred to a dry and sealed glove box. The mixed powder was then ground and placed in a tube furnace using a small crucible. The product was heated to 800 °C at a rate of 10 °C min^{−1} in an argon environment

and calcined for 12 h. After calcination, the sample was ground into a black powder using a mortar, and the resulting sample was named TaS₂-12-800. Similarly, samples TaS₂-12-900 and TaS₂-12-1000 were synthesized using the same method with calcination temperatures of 900 °C and 1000 °C, respectively. The TaS₂ samples synthesized at high temperatures could have the 3R phase. For comparison on the influence of calcination time on the samples, some samples were synthesized at 800, 900, and 1000 °C for 24 h and were denoted as TaS₂-24-800, TaS₂-24-900, and TaS₂-24-1000.

2.2. Characterizations

The analysis was performed using a Nippon Rigaku Smart Lab Diffractometer (Japan) for X-ray diffraction measurements. Scanning electron microscopy (SEM) and energy-dispersive X-ray spectroscopy (EDS) were carried out on a Hitachi S-3400 instrument (Japan). The morphologies and crystal structures of the as-synthesized products were investigated using a Hitachi H-7650 transmission electron microscope (TEM, Japan) and a high-resolution transmission electron microscope (HR-TEM, FEI Tecnai F20, USA). X-ray photoelectron spectroscopy (XPS) was employed for both qualitative and quantitative analyses of the elements, utilizing an ESCALAB 250Xi instrument of Thermo Company (USA). Nitrogen adsorption and desorption isotherms were analyzed using a Mack ASAP2420 nitrogen adsorption meter (USA). The specific surface area was determined using the Brunauer Emmett Teller (BET) method, while the pore size distribution was calculated using the Barrett Joyner Helena (BJH) model. The electromagnetic absorption effectiveness of the samples in the frequency range of 2–18 GHz was assessed using a coaxial method and a vector network analyzer (VNA, MS-200644A ANRITSU, Japan) was used for the measurement. The absorbers containing 60 wt% paraffin and 40 wt% of TaS₂ samples were prepared and compressed into rings with an inner diameter of 3 mm, an outer diameter of 7 mm, and a thickness of 2 mm. The electrical conductivity of the compressed material was measured at room temperature using the four-probe technique.

3. Results and discussion

The schematic of synthesis of stacked TaS₂ nanosheets is depicted in Fig. 1. TaCl₅ is used as the tantalum source and CH₃CSNH₂ is used as the sulfur source for the formation of TaS₂ nanosheets. During the reaction, Ta and S ions are combined to form Ta–S–Ta clusters through covalent bonding. These clusters act as nuclei for the formation of TaS₂ nanosheets, resulting in a stacked nanosheet-like structure with a small thickness and definitive profile. When synthesized at high temperatures, TaS₂ exhibits the characteristics of a 3R-type structure, which is relatively stable.

The composition and structure of 3R-TaS₂ are analyzed using an X-ray diffractometer. As shown in Fig. 2(a and b). The characteristic peaks of 3R-TaS₂ are found at 14.84°, 31.49°, and 55.29°, corresponding to crystal planes (003), (101), and (110), respectively [35,36]. The main diffraction peak of 3R-TaS₂ is sharp and high, indicating that the sample has good purity and crystallinity. It should be noted that there are some oxidation peaks in the 20–30° range for samples TaS₂-12-800, TaS₂-12-900, TaS₂-24-800, and TaS₂-24-900. These peaks correspond to Ta₂O₅ (PDF #71–0639).

The XPS spectra of 3R-TaS₂ are shown in Fig. S1, which provide information about the composition and chemical states of the elements in the samples. The presence of oxygen on the sample surface leads to the formation of Ta₂O₅, which coexists with 3R-TaS₂. With increasing calcination temperature, a large number of nanosheet layers are tightly aggregated, resulting in weakening of the peak intensity for Ta₂O₅. The results reveal the presence of five major elements (Ta, S, C, N, and O). A small amount of impurities, N and C, are detected in the sample, which could be attributed to the thermal decomposition of CH₃CSNH₂ during preparation and the formation of residual elements C and N on the

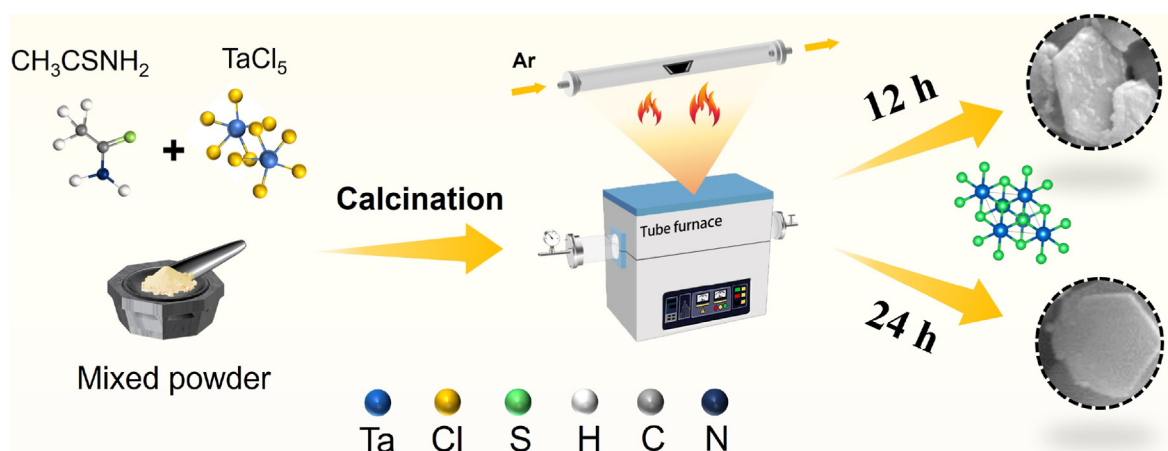


Fig. 1. Preparation process of 3R-TaS₂.

sample surface. Fig. 2(c and d) clearly shows the high-resolution XPS spectra of Ta and S, providing information about their content and chemical states [37,38]. Due to the susceptibility of the TaS₂ powder surface to oxidation, a strong peak of Ta⁵⁺ belonging to Ta₂O₅ is observed in Fig. 2(c), indicating that Ta⁵⁺ exists in oxide impurities on sample surface only [39], while Ta⁴⁺ is attributed to TaS₂ [35]. In order to analyze the specific surface area and pore size distribution of TaS₂, we conducted N₂ adsorption and desorption isotherms along with pore size tests, as illustrated in Fig. S2. The isotherms and hysteresis lines of TaS₂-12-800, TaS₂-12-900, TaS₂-12-1000, TaS₂-24-800, TaS₂-24-900, and TaS₂-24-1000 demonstrate IV-type behavior, indicating the presence of mesoporous pores. Specifically, TaS₂-24-1000 exhibits a pore size concentration at 4.77 nm, with the mesoporous structure significantly enhancing the material's specific surface area to 113.2 m² g⁻¹. Furthermore, this mesoporous structure also contributes positively to the material's ability to attenuate electromagnetic waves.

The topography of the TaS₂ nanosheets is examined using scanning electron microscopy (SEM) and transmission electron microscopy (TEM). In Fig. 3(a), the TaS₂-12-1000 nanosheets display a lamellar polygonal structure, and the mapping images (Fig. 3(b and c)) confirm the uniform distribution of elements. As the calcination temperature is increased and the calcination time is extended, the morphology of nanosheets are gradually transformed into a stacking mode, forming a structure that promotes multiple reflections and repeated absorption of electromagnetic waves. Similar polygonal morphological characteristics are observed in TaS₂-24-1000 (Fig. 3(d–f)). Previous studies have discussed the crystal growth mechanisms of the samples, suggesting that the sheet growth mechanism may not be influenced by the movement of the layer faults during growth. In 3R-TaS₂, the Ta atom is coordinated with six S atoms. When there is an excess of Ta atoms, lattice expansion occurs along the stacking direction, leading to a change in the distance between adjacent Ta–S atoms [40,41] and consequently altering the TaS₂ morphology (Fig. 3(g and h)). The lattice spacing of the TaS₂ samples is analyzed using high-resolution TEM (HRTEM) methods, revealing a regular arrangement of TaS₂ layers with a layer spacing of 0.68 nm (Fig. 3(i)). To obtain more accurate inter-layer spacing (*d* values) corresponding to the crystal planes as estimated from X-ray diffraction analysis, the *d* values of TaS₂ in Fig. 3(j) are determined by HRTEM to be 0.27 nm, and 0.28 nm, respectively, corresponding to the (012), and (101) crystal planes of 3R-TaS₂. Fig. 3(k) illustrates the sample characteristics with a lattice spacing of 0.24 nm, corresponding to the (104) crystal facets. HRTEM images demonstrate that 3R-TaS₂ is a highly crystalline polycrystalline material.

The EMW absorption performance of microwave-absorbing materials is characterized by the reflection loss (RL), and the electromagnetic compatibility of the as-prepared sample can be evaluated based on the RL

value, which is calculated using the formula derived from transmission line theory, as follows [42]:

$$RL = 20 \cdot \log_{10} \left| \frac{Z_{in} - Z_0}{Z_{in} + Z_0} \right| \quad (1)$$

where the normalized input impedance (*Z*_{in}) is given by:

$$Z_{in} = Z_0 \sqrt{\frac{\mu_r}{\epsilon_r} \tanh \left(j \left(\frac{2\pi f d}{c} \right) \sqrt{\mu_r \epsilon_r} \right)} \quad (2)$$

where *Z*_{in} represents the normalized input impedance of the absorber, *Z*₀ represents the free space impedance, *d* is the thickness of the absorber, *c* is the speed of light in a vacuum, *f* is the frequency of microwaves, ϵ_r represents the permittivity and $\epsilon = \epsilon' - j\epsilon''$, μ_r is the relative complex permeability and $\mu = \mu' - j\mu''$.

The relationship between the absorbing layer thickness (*t*_m) and the corresponding absorption peak frequency (*f*_m) can be described by a quarter-wavelength (1/4) model with the following formula [43–45]:

$$t_m = \frac{n\lambda}{4} = \frac{nc}{4f_m \sqrt{|\epsilon_r \mu_r|}} \quad (n = 1, 3, 5 \dots) \quad (3)$$

where *n* is the wavenumber, λ is the wavelength of the microwave.

To better understand the mechanisms of microwave absorption, the simulated thickness of TaS₂ determined using the 1/4 model is compared with the actual sample thickness. The results (Fig. 4) reveal that unlike traditional microwave absorbing materials, samples synthesized at 24 h exhibit dual-frequency absorption. Similarly, samples synthesized at 800, 900, and 1000 °C for 12 h also show dual-frequency absorption, but to a lesser extent. The dual-band absorption peaks are observed in the C-band and K_u-band, with the minimum reflection loss shifting from the high-frequency to the low-frequency region as the calcination temperature increased. With these variations, we can find that the sample thickness meets the conditions of one-quarter wavelength.

In this study, we successfully synthesize TaS₂ samples by adjusting the calcination temperature and time. From Fig. 4(a and b), it is observed that the RL levels for TaS₂-12-800 and TaS₂-12-900 samples are below −10 dB at the thickness of 5–5.5 mm, while at other thicknesses, the levels barely reach −10 dB. The results can be attributed to the presence of Ta₂O₅ in the sample, which limits its effectiveness in the low frequency region. As depicted in Fig. 4(c), when the calcination temperature is increased, TaS₂-12-1000 samples with thicknesses varying from 1.5 mm to 5.5 mm show an effective absorption bandwidth of approximately 2.96–12.72 GHz and 13.44–18 GHz, with a minimum reflection loss (RL_{min}) of −29.5 dB. Samples synthesized at an extension of the reaction time are analyzed as well, with results shown in Fig. 4(d and e), revealing

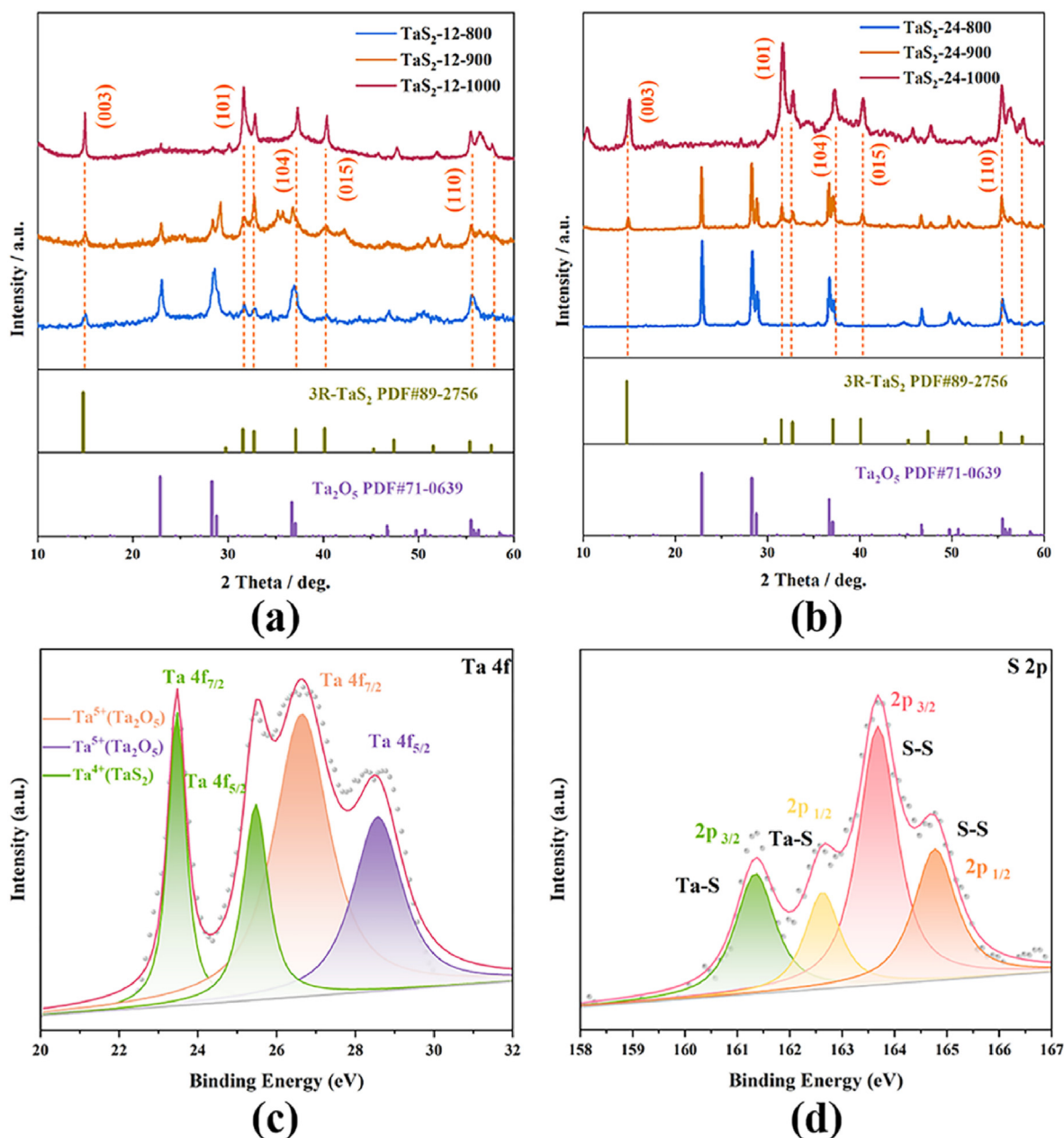


Fig. 2. XRD patterns of (a) TaS₂-12-800, TaS₂-12-900, and TaS₂-12-1000 and (b) XRD patterns of TaS₂-24-800, TaS₂-24-900, TaS₂-24-1000; High-resolution XPS scans of (c) Ta and (d) S.

that the $RL_{\min}$ values for TaS₂-24-800 and TaS₂-24-900 samples occur in the low-frequency region, with values of -25.9 dB and -21.5 dB, respectively. Fig. 4(f) demonstrates that the TaS₂-24-1000 sample achieves an effective absorption bandwidth 3.92–16.56 GHz, with an $RL_{\min}$ value of -39.8 dB at a thickness of 5.5 mm. These findings suggest that the optimization on the calcination temperature and time could lead to a dense structure of TaS₂, enhancing interface polarization between Ta₂O₅ and TaS₂ and facilitating charge redistribution, which ultimately improves the capacity for electromagnetic wave absorption.

To further analyze the electromagnetic wave attenuation performance of the samples, the thickness of absorbers is refined. Fig. 5(a and b) illustrates that $RL_{\min}$ of the TaS₂-12-1000 sample, with a thickness ranging from 1.82 to 2.32 mm, reaches -30.6 dB within the 11–11.5 GHz range at a specific thickness of 2.02 mm. Similarly, Fig. 5(c and d) show that the RL level of the TaS₂-24-1000 sample, with a thickness of 5.3–5.8 mm, is as low as -41.4 dB at 4–4.5 GHz at a thickness of 5.6 mm. In summary, as shown in Table 1, the TaS₂ samples developed in this work

exhibit excellent electromagnetic wave absorption performance [6, 11–14, 16, 52–62].

For a deeper examination on the electromagnetic wave absorption process, the material's dielectric properties across a 2–18 GHz frequency spectrum are analyzed, utilizing the following formula [46]:

$$\varepsilon_r = \varepsilon_\infty + \frac{\varepsilon_s - \varepsilon_\infty}{1 + j2\pi f\tau} = \varepsilon' - j\varepsilon'' \quad (4)$$

where ε' is the real part of the complex permittivity, related to the storage capacity of electricity, ε'' is the imaginary part of the complex permittivity, which is related to energy loss.

Based on the data presented in Fig. 6(a) and (d), we observe that the real part of the permittivity, ε' , for the TaS₂ EMW absorbing material, decreases with increasing frequency. This trend could be due to the slower response of dipoles at higher frequencies, which leads to reduced storage capacity for electric energy, as indicated by the decrease in ε' . The

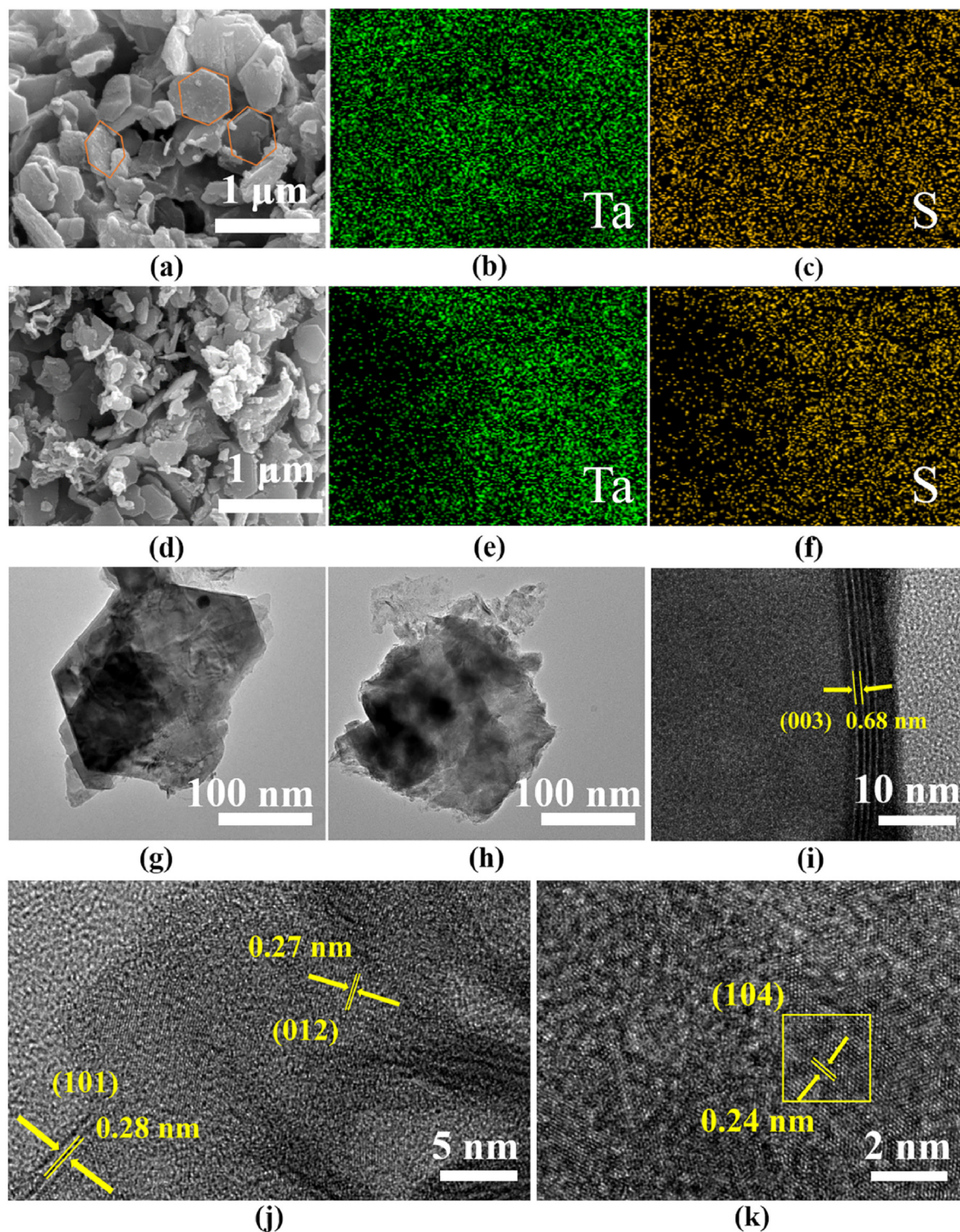


Fig. 3. SEM and TEM images of TaS₂ with corresponding element mapping diagrams: (a) SEM image of TaS₂-12-1000 and the corresponding element mapping diagrams for (b) Ta and (c) S; (d) SEM image of TaS₂-24-1000 and the corresponding element mapping diagrams for (e) Ta and (f) S. TEM images of (g) TaS₂-12-1000 and (h) TaS₂-24-1000. HRTEM images of TaS₂-24-1000 showing the interlayer spacing in regions of 3R-TaS₂: (i), (j), and (k).

results suggests that the attenuation mechanism affecting the RL peak primarily involves polarization relaxation, as indicated by the changes in the imaginary part of the dielectric constant.

In general, the real part of the dielectric constant (ϵ') represents the material's capacity to store electric energy, while the imaginary part (ϵ'') indicates how effectively the material can dissipate the energy [47]. Additionally, the ratio of the imaginary part to the real part, known as

tangent ($\tan\delta\epsilon$), is a crucial factor in evaluating the characteristics of the sample. Based on the results shown in Fig. 6(b) and (e), it can be observed that for samples prepared at high reaction temperatures, the imaginary part of the dielectric constant initially increases and then decreases. The comparison between the dielectric constant imaginary part and the reflection loss curve, as depicted in Figs. S3(a–f), indicates an inverse relationship between the RL values and frequency. This suggests that the

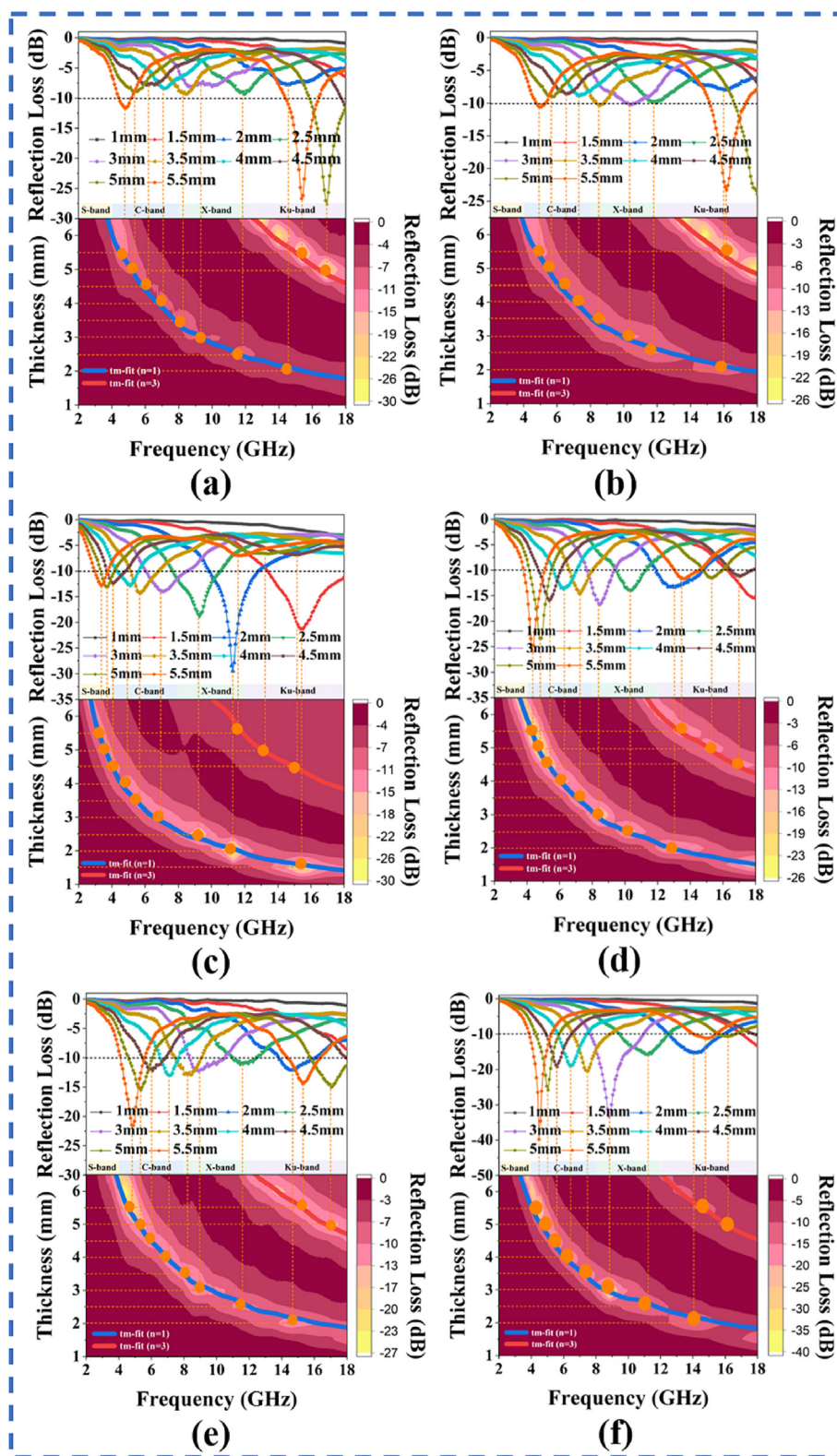


Fig. 4. Reflection loss curves and corresponding quarter-wavelength and three-quarter wavelength matching curves for TaS₂ samples calcined at different temperatures: (a) TaS₂-12-800, (b) TaS₂-12-900, (c) TaS₂-12-1000, (d) TaS₂-24-800, (e) TaS₂-24-900, and (f) TaS₂-24-1000.

attenuation observed during RL measurements is influenced by variations in the imaginary part of the dielectric constant. Notably, TaS₂-12-1000 and TaS₂-24-1000 samples synthesized at a reaction temperature of 1000 °C exhibit a higher dielectric constant. These samples are capable of converting the energy of incident electromagnetic waves

into other forms of energy to absorb electromagnetic waves effectively. Hence, it can be concluded that a larger imaginary part of the dielectric constant corresponds to better microwave absorption performance of the sample. Furthermore, as observed in Fig. 6(c) and (f), the $\tan\delta\epsilon$ values for the TaS₂-12-800, 900, 1000 and TaS₂-24-800, 900, 1000 samples are

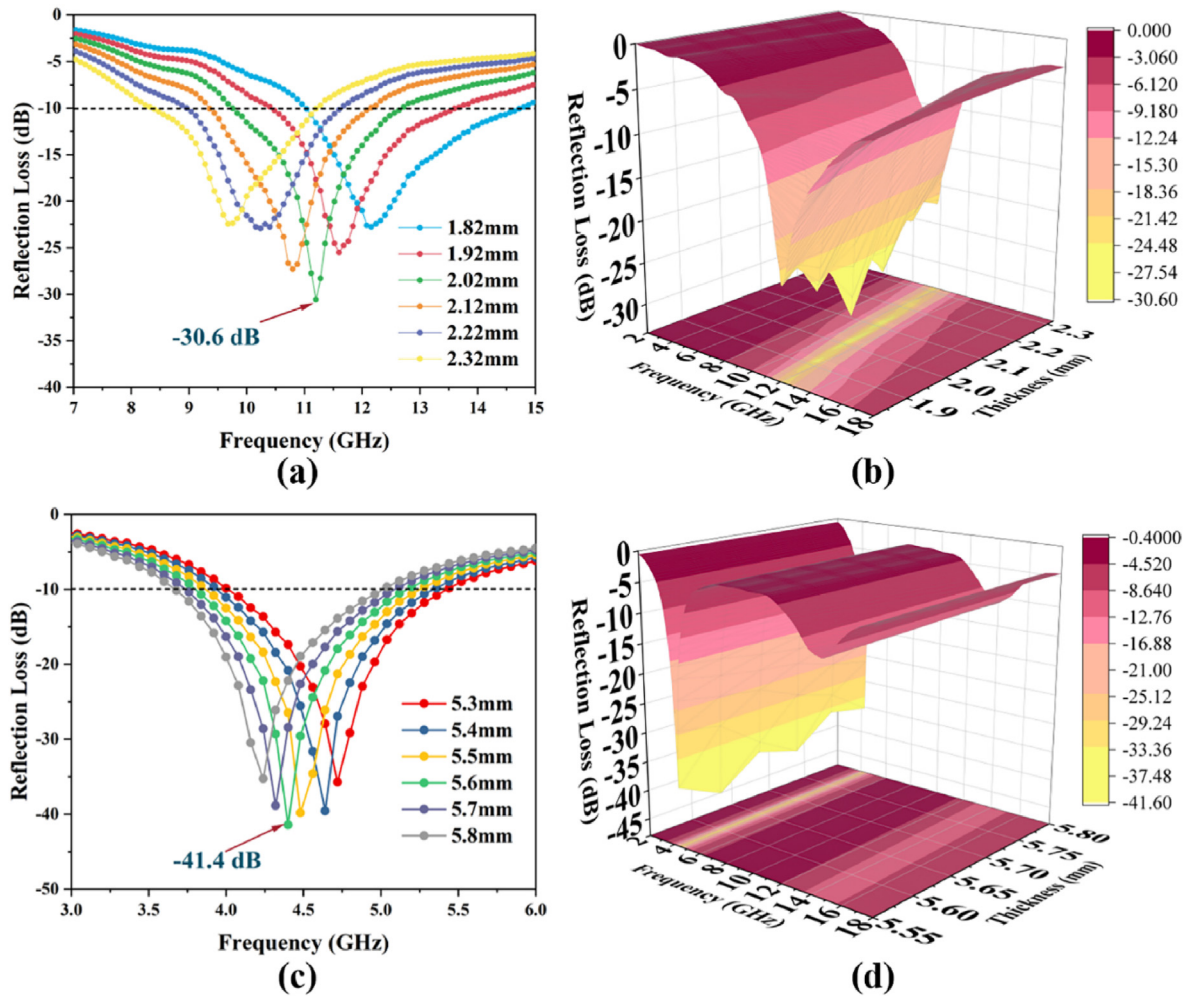


Fig. 5. TaS₂ sample reflection loss (RL) analysis: (a) RL values for TaS₂-12-1000 with thicknesses varying from 1.82 to 2.32 mm; (b) 3D representation of RL changes for the sample in (a); (c) RL values for TaS₂-24-1000 with thicknesses varying from 5.3 to 5.8 mm; (d) 3D representation of RL changes for the sample in (c).

Table 1
Comparative analysis of EMW absorption properties of TMDs prepared in this work and those reported in literature.

Materials	Loading ratio (wt %)	RL (dB)	Frequency (GHz)	Thickness (mm)	RL _{min} (dB)	Frequency (GHz)	Thickness (mm)	Ref.
TaS ₂ -12-1000	40	-29.5	11.28	2	-30.6	11.2	2.02	This Work
TaS ₂ -24-1000	40	-39.8	4.48	5.5	-41.4	4.4	5.6	This Work
VS ₂	40	-33.8			-57.4	4	5.75	[6]
VS ₂ -NiO	20			1.5	-58.98	12.32	1.48	[11]
VS ₂ /GDC	40	-37.4		5.5	-52.8	12.2	2.7	[12]
C/VS ₂	75	-54.32	13.4	1.9	-62.74	14.56	1.7	[13]
VS ₂ /Co ₃ O ₄	40				-57.96	12.8	1.57	[14]
NbS ₂	40	-43.5	11.2	2.5				[16]
3D MoS ₂	25	-26.1	11.36	2.5				[52]
WS ₂	30	-37	4.3	6	-63	12.1	2.5	[53]
WS ₂ @BDC	40	-51.4	5.52	4.5				[54]
WS ₂ /Co	50	-19.8	2.48	4	-46.5	10.2	1.7	[55]
MoS ₂ /Ti ₃ C ₂ T _x	96.104	-31.59		5	-61.65		4.53	[56]
C/MoS ₂	25	-55.12	12.44	2.06	-75.94	16.2	1.68	[57]
MoS ₂ /CoS ₂ /VN	40				-50.48		2.02	[58]
CoTe ₂ @MoS ₂	50	-45.8	15	1.6	-68.10	4.71	4.5	[59]
SiC _t @WS ₂	15	-49.88		2.8	-72.76	12.74	2.86	[60]
MoS ₂ /Si ₃ N ₄		-31.01	8.47	4.6	-68.66		3.06	[61]
Si ₃ N ₄ @WS ₂		-23.83	8.2	4.94	-65.03	9.17	4.35	[62]

0.20, 0.20, 0.51, 0.30, 0.28, 0.33, respectively, and those samples calcined at 1000 °C for 12 h or 24 h, possess higher $\tan\delta\epsilon$ values than other samples.

It is suggested that the increase in the imaginary part of the dielectric constant indicates the enhanced electromagnetic wave attenuation, po-

larization, and relaxation properties of the sample, which could be verified by a detailed analysis on the Debye relaxation process. The relationship between ϵ' and ϵ'' can be described by the following formula [48,49]:

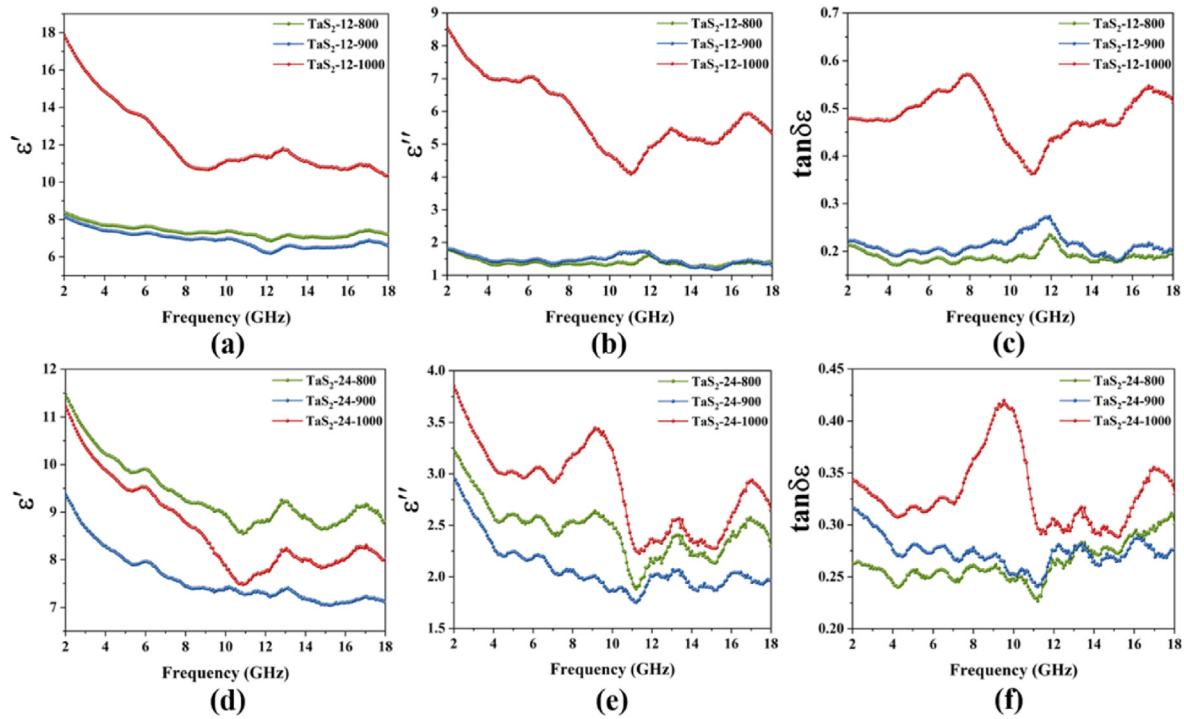


Fig. 6. Dielectric properties of TaS₂ samples: (a) real part and (b) imaginary part of the complex dielectric constant, and (c) dielectric loss tangent for TaS₂-12-800, 900, 1000; (d) real part and (e) imaginary part of the complex dielectric constant, and (f) dielectric loss tangent for TaS₂-24-800, 900, 1000.

$$\varepsilon' = \varepsilon_{\infty} + \frac{\varepsilon_s - \varepsilon_{\infty}}{1 + (2\pi f)^2 \tau^2} \quad (5)$$

$$\varepsilon'' = \frac{\varepsilon_s - \varepsilon_{\infty}}{1 + \omega^2 \tau^2} \omega \tau + \frac{\sigma}{\omega \varepsilon_0} \quad (6)$$

where ω is the angular frequency, f is the frequency, τ is the polarization relaxation time, ε_s is the static permittivity, and ε_{∞} is the relative permittivity at infinite frequency. Thus, the relationship between ε' and ε'' is given by the following formula [50]:

$$\left(\varepsilon' - \frac{\varepsilon_s + \varepsilon_{\infty}}{2}\right)^2 + (\varepsilon'')^2 = \left(\frac{\varepsilon_s - \varepsilon_{\infty}}{2}\right)^2 \quad (7)$$

In the Cole-Cole plots (Fig. 7(a and b)), each downward semicircle represents a Debye relaxation process, indicating a microwave absorption process. For samples synthesized at reaction temperatures of 800 °C and 900 °C, no Debye relaxation process is evident in the Cole-Cole plots (Fig. S4). However, for the TaS₂-12-1000 samples synthesized at 1000 °C, two Debye-like relaxation processes are observed. In Fig. 7(a), the relaxation of the TaS₂-12-1000 sample occurs at frequencies of 7.6 GHz and 6.2 GHz, which are consistent with the change in frequency shown in the figure for ε'' (dielectric imaginary part). In Fig. 7(b), the TaS₂-24-1000 sample exhibits multiple relaxation processes at frequencies of 9.3 GHz, 7.76 GHz, and 5.84 GHz. The generation of multiple polarization relaxation processes can be attributed to the presence of Ta and S vacancies in the material, which create dipoles at the defect locations, resulting in

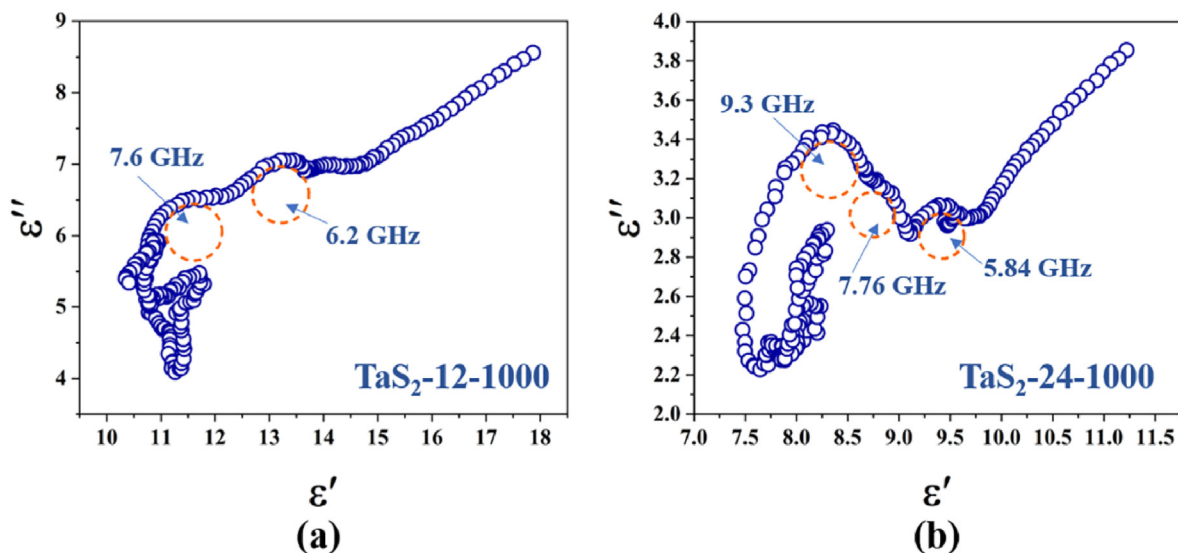


Fig. 7. Cole-Cole curves for TaS₂ samples: (a) TaS₂-12-1000, (b) TaS₂-24-1000.

dipole polarization and attenuation of electromagnetic waves.

A efficient microwave absorber is characterized by its substantial ability to dampen microwave signals. The efficacy of EMW dampening is measured by the attenuation constant (α) as follows [51]:

$$\alpha = \frac{\sqrt{2}\pi f}{c} \times \sqrt{(\mu''\epsilon'' - \mu'\epsilon') + \sqrt{(\mu''\epsilon'' - \mu'\epsilon')^2 + (\epsilon'\mu'' + \epsilon''\mu')^2}} \quad (8)$$

The calculated α is directly compared with the values obtained from experimental data. Notably, the α value for the sample exhibits an increasing trend with increasing frequency. In Fig. S5(a), the α value of TaS₂-12-1000 reaches a maximum value of 267.63, which is greater than those of the samples TaS₂-12-800 and TaS₂-12-900. In Fig. S5(b), the α value of TaS₂-24-1000 reaches a maximum value of 159.59, which is greater than those of the samples TaS₂-24-800 and TaS₂-24-900. It is evident that α values of the samples TaS₂-12-1000 and TaS₂-24-1000 exhibit a rapid growth in the frequency range of 2–10 GHz, indicating their good attenuation performance for EMW absorption. The results are consistent with the those obtained from the RL curves. Based on the analysis described above, it can be concluded that the EMW absorption ability of samples TaS₂-12-1000 and TaS₂-24-1000 is related with their calcination time.

Strong absorption loss capacity is a necessary condition for the material to exhibit a significant RL value (in dB), and good impedance matching (M_z) is the primary condition for EMW to penetrate the absorber. These two values are extremely important electromagnetic wave absorption parameters. According to the theory, when the characteristic impedance Z_{in} of the material is close to the free space impedance Z_0 , the electromagnetic radiation can be absorbed to the maximum extent and zero reflection can be achieved on the surface of the material. M_z can be estimated using the following formula [63]:

$$M_z = \frac{Z'_{in}}{|Z_{in}|^2 + 1} \quad (9)$$

where Z'_{in} is the real part of the normalized input impedance. In general, when M_z becomes very close to 1, the characteristic impedance matching of the material increases, and specifically, most of the incident electromagnetic waves enter the material.

Through the analysis of the dielectric constant, $\tan\delta\epsilon$, and Cole-Cole curves, it is observed that the samples TaS₂-12-1000 and TaS₂-24-1000 perform well in EMW absorption. Furthermore, the impedance matching is tested for the samples, focusing on determining significant changes in the attenuation constant (α) within the 2–18 GHz range. In Fig. 8(a and b), the impedance matching values of TaS₂-12-800 and TaS₂-12-900 do not reach 1, proving that electromagnetic waves do not enter the material efficiently and the dielectric properties of samples are not improved. In Fig. 8(c), TaS₂-12-1000 exhibits an absorption loss RL close to 1 with the thicknesses of 1.5–5.5 mm, which indicates that the material efficiently absorbs most incident electromagnetic waves and the absorption is maximized without reflection as the waves propagate further. It is worth noting that TaS₂-12-1000 does not achieve perfect impedance matching in the low-frequency region. In contrast, as shown in Fig. 8(d–f), TaS₂-24-1000 achieves a close-to 1 RL value with the thicknesses of 2–5.5 mm and impedance matching is perfectly achieved in the low-frequency region. This finding highlights the strong EMW absorption in the low-frequency bands could be achieved in the samples. When the impedance matching is close to 1, the attenuation constant α reaches a maximum value of 159.59, indicating excellent impedance matching and strong electromagnetic wave attenuation ability.

The in-depth investigation of the application of VB-group TMDs with unique physical and chemical properties in EMW absorbing materials is imperative [64]. The attenuation mechanism of stacked TaS₂ nanosheets can be summarized as follows. Firstly, the impedance matching of the absorption system ensures that the incident wave can enter the absorber to its maximum extent. As shown in Fig. 9, when the electromagnetic wave reaches the surface of the TaS₂ nanosheets, it enters the absorber as much as possible. The multi-interface structure of TaS₂ induces dipole and interfacial polarization effects, causing the nanosheets to absorb electromagnetic energy through dipole polarization and polarization relaxation [65]. This leads to multiple reflections and absorption of electromagnetic waves between the material nanosheets, ultimately increasing the propagation path and enhancing the attenuation of internal electromagnetic waves [66]. Furthermore, TaS₂ nanosheets possess good electrical conductivity but still exhibit some resistances. Consequently, the joule heating resulting from currents generated by microwave radiation in the materials could convert microwave energy

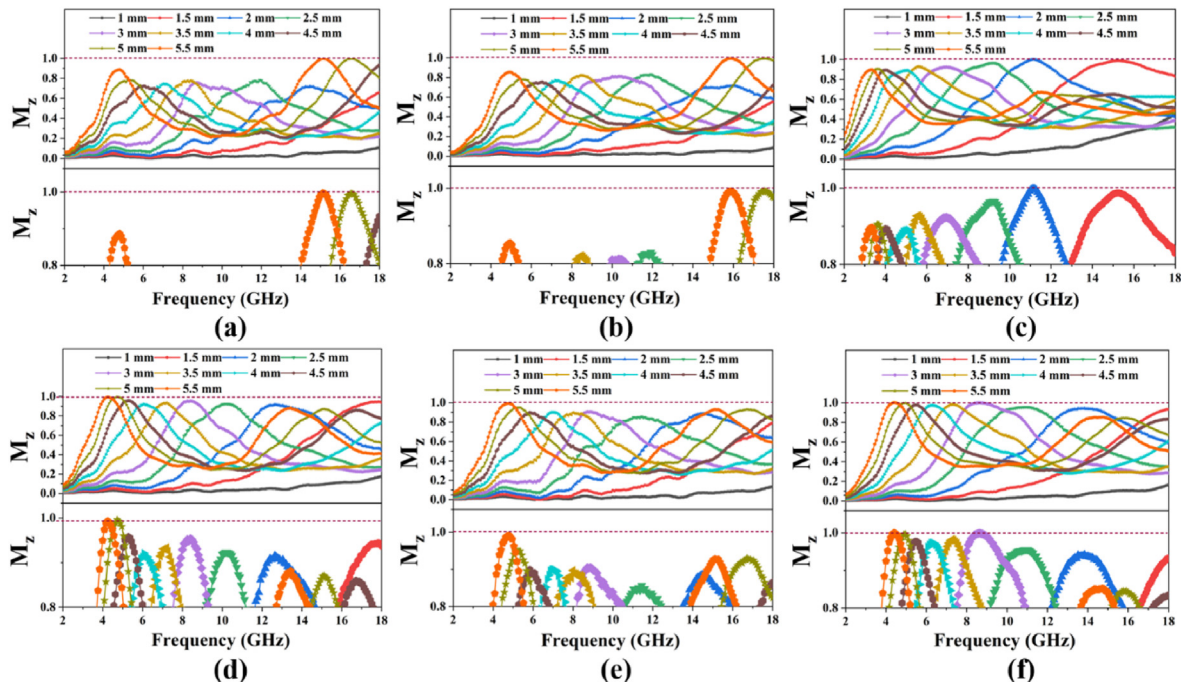


Fig. 8. Impedance matching coefficients of (a) TaS₂-12-800, (b) TaS₂-12-900, (c) TaS₂-12-1000, (d) TaS₂-24-800, (e) TaS₂-24-900, and (f) TaS₂-24-1000.

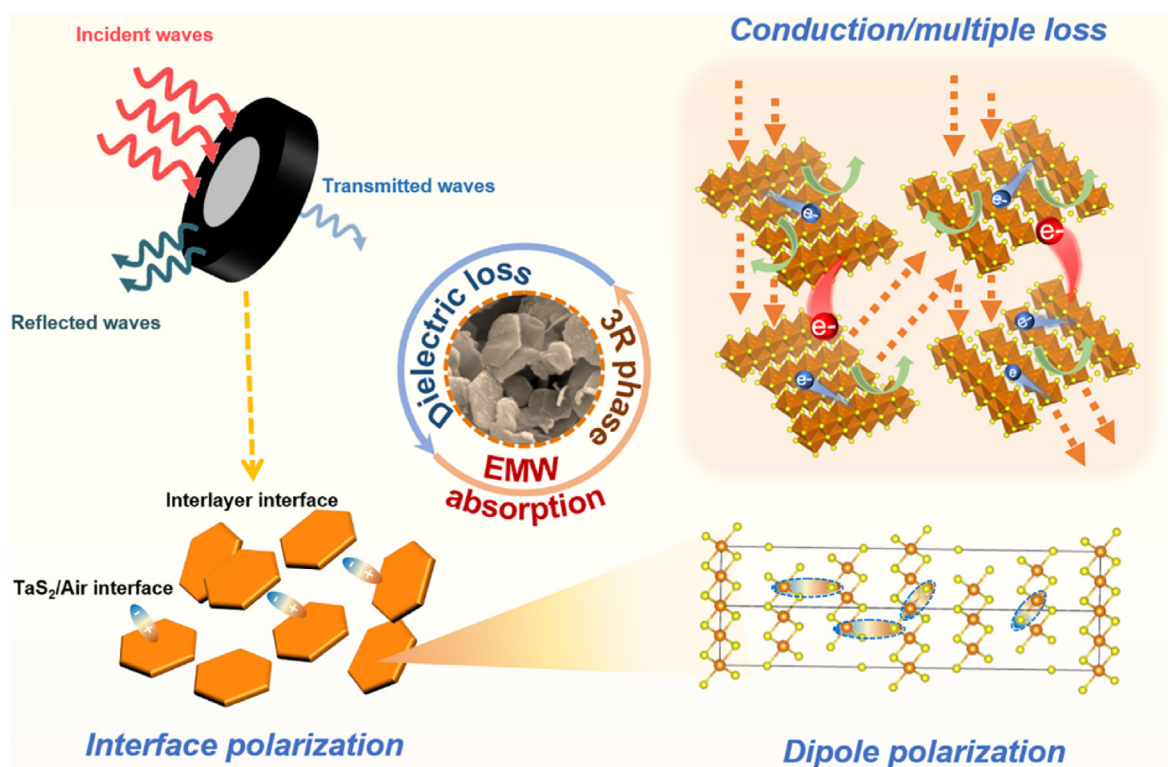


Fig. 9. Schematic diagram of the electromagnetic absorption mechanisms of TaS₂ nanosheets.

into heat energy. Additionally, the electrons generated by microwave radiation can jump between TaS₂ nanosheets, resulting in the dissipation of electromagnetic energy. Therefore, under the synergistic effect of multiple reflections, dipole polarization, and interfacial polarization, TaS₂ nanosheets have excellent EMW absorption performance.

4. Conclusions

In summary, for the first time TaS₂ nanosheets exhibiting outstanding microwave absorption performance are successfully synthesized through a carefully controlled calcination process. By precisely tailoring the thickness of the absorbers, significant microwave absorption across both the C-band and Ku-band is attained. The minimum RL values are exceptionally low, reaching −41.4 dB within the 4–4.5 GHz range. The TaS₂-24-1000 nanosheets, in particular, show superior microwave absorption efficiency, especially within the C-band, demonstrating their promising potential for practical applications. Remarkably, all the TaS₂ nanosheets prepared in this work possess dual-band absorption capability, which is a highly desirable feature for multi-frequency electromagnetic interference shielding. Furthermore, it is revealed that the surface morphology of nanosheets can be tuned by varying the reaction conditions, indicating a controllable synthesis process that could be further optimized. Although the calcination method employed is not novel, the exceptional performance of the resultant TaS₂ nanosheets establishes a solid foundation for the advancements of EMW absorption in TMDs. This work underscores the significant potential of TaS₂-based materials in designing new, efficient composite microwave absorbers.

Declaration of competing interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

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Appendix A. Supplementary data

Supplementary data to this article can be found online at <https://doi.org/10.1016/j.nanoms.2024.05.011>.

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